IN THE CLAIMS:

Please cancel claim 18-39, drawn to a non-elected invention, without prejudice.

Please amend the claims with the replacement claims presented below.

Please add claims 40-55.

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1. (Original) A method for processing a substrate, comprising:

providing a substrate with feature definitions formed in a dielectric material;

depositing a barrier layer material on a substrate surface and in the feature definitions;

depositing a first conductive material on the barrier layer material to fill the feature definitions;

polishing the first conductive material to at least a top surface of the barrier layer material;

depositing a second conductive material by an electrochemical deposition technique on at least the first conductive material to fill recesses formed in the first conductive material; and

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polishing the second conductive material and the barrier layer material to at least a top surface of the dielectric layer to form a planar surface.

2. (Currently Amended) The method of claim 1, wherein the first conductive material comprises copper, aluminum, tungsten, or combinations thereof.

3. (Original) The method of claim 1, wherein the second conductive material comprises a noble metal, a semi-noble metal, a group IVA metal, or combinations thereof.

4. (Currently Amended) The method of claim 1 ~~3~~, wherein the second conductive material is selected from the group of copper, platinum, nickel, tin, cobalt, palladium, gold, silver, osmium, iridium, rhenium, ruthenium, aluminum, tungsten, and combinations thereof.

5. (Original) The method of claim 1, wherein the electrochemical deposition technique comprises an electroplating deposition technique, an electroless deposition technique, or an electrochemical mechanical plating process technique.

6. (Original) The method of claim 1, wherein the second conductive material is deposited to a thickness between about 25 Å and about 2000 Å.

7. (Original) The method of claim 1, further comprising depositing a conductive seed layer on the barrier layer material by a chemical vapor deposition technique or a physical vapor definition technique prior to depositing the first conductive material.

8. (Original) The method of claim 1, further comprising annealing the substrate.

9. (Original) The method of claim 1, further comprising rinsing the substrate after each polishing process.

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10. (Original) The method of claim 1, wherein polishing the first conductive material, depositing the second conductive material, and polishing the second conductive material and the barrier layer material are performed in the same polishing system.

11. (Original) The method of claim 1, wherein depositing the second conductive material and polishing the second conductive material and the barrier layer material are performed concurrently.

12. (Original) A method for planarizing a substrate surface, comprising:

providing a substrate to a polishing station disposed on a processing system, wherein the substrate comprises a dielectric material with substrate feature definitions formed therein, a barrier layer material disposed thereon and within the feature definitions, and a copper material disposed on the barrier layer material;

polishing a copper material from the substrate surface to at least a top surface of the barrier layer material;

transferring the substrate to an electrochemical deposition and polishing station disposed on the polishing system;

depositing a conductive material selectively on the copper containing material by an electroless deposition technique while removing the conductive material and the barrier layer material to at least a top surface of the dielectric layer by a polishing technique.

13. (Original) The method of claim 12, wherein the conductive material is deposited to a thickness between about 25 Å and about 2000 Å.

14. (Original) The method of claim 12, wherein the conductive material is selected from the group of a noble metal, a semi-noble metal, a group IVA metal, and combinations thereof.

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15. (Currently Amended) The method of claim 12 ~~14~~, wherein the conductive material is selected from the group of copper, platinum, nickel, tin, cobalt, palladium, gold, silver, osmium, iridium, rhenium, ruthenium, aluminum, tungsten, and combinations thereof.

16. (Original) The method of claim 12, further comprising annealing the substrate after polishing the second conductive material and the barrier layer material to the top surface of the dielectric layer.

17. (Original) The method of claim 12, further comprising rinsing the substrate after each polishing process.

18. (Cancelled)

19. (Cancelled)

20. (Cancelled)

21. (Cancelled)

22. (Cancelled)

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26. (Cancelled)

27. (Cancelled)

28. (Cancelled)

29. (Cancelled)

30. (Cancelled)

31. (Cancelled)

32. (Cancelled)

33. (Cancelled)

34. (Cancelled)

35. (Cancelled)

36. (Cancelled)

37. (Cancelled)

38. (Cancelled)

39. (Cancelled)

Please add the following claims:

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40. (New) The method of claim 1, wherein the electrochemical deposition technique is an electroless deposition technique and the first conductive material and the second conductive material are copper.

41. (New) The method of claim 1, wherein the electrochemical deposition technique is an eletroplating deposition technique and the first conductive material and the second conductive material are copper.

42. (New) The method of claim 1, wherein the first conductive material is different from the second conductive material.

43. (New) The method of claim 1, wherein the first conductive material is the same as the second conductive material.

44. (New) The method of claim 1, wherein the first conductive material is selectively polished as compared to the barrier layer material.

45. (New) The method of claim 1, wherein the second conductive material is selectively deposited on the first conductive material in recess as compared to the barrier layer material.

46. (New) The method of claim 1, wherein polishing the first conductive material and depositing the second conductive material are performed concurrently by an electrochemical mechanical plating technique.

47. (New) A method for planarizing a substrate surface, comprising:

providing a substrate to a polishing station disposed on a processing system, wherein the substrate comprises a dielectric material with substrate feature definitions formed therein, a barrier layer material disposed thereon and within the feature definitions, and a copper material disposed on the barrier layer material;

polishing a copper material from the substrate surface to at least a top surface of B1 the barrier layer material;

depositing a conductive material selectively on the copper material by an electrochemical deposition technique;

polishing the conductive material and the barrier layer material to at least a top surface of the dielectric layer by a polishing technique.

48. (New) The method of claim 47, wherein the electrochemical deposition technique comprises an electroplating deposition technique, an electroless deposition technique, or an electrochemical mechanical plating technique.

49. (New) The method of claim 47, wherein polishing the copper material and depositing the second conductive material are performed concurrently by an electrochemical mechanical plating technique.

50. (New) The method of claim 47, wherein the electrochemical deposition technique is an electroless deposition technique and the conductive material is copper.

51. (New) The method of claim 47, wherein the electrochemical deposition technique is an eletroplating deposition technique and the conductive material is copper.

52. (New) The method of claim 47, wherein the conductive material is not copper.

53. (New) The method of claim 47, wherein the conductive material is selected from the group of copper, platinum, nickel, tin, cobalt, palladium, gold, silver, osmium, iridium, rhenium, ruthenium, aluminum, tungsten, and combinations thereof.

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54. (New) The method of claim 47, wherein the copper material is selectively polished as compared to the barrier layer material.

55. (New) The method of claim 47, wherein the second conductive material is selectively deposited on the first conductive material in recess as compared to the barrier layer material.